**THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**REVOCATION AND NEW POWER OF ATTORNEY AND CHANGE OF CORRESPONDENCE ADDRESS**

I, ***Dr. Graham Fisher, Director of Intellectual Property*** of ***MEMC Electronic Materials, Inc.***, the Assignee of the entire right, title, and interest in the ***U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A***, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the ***U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A:***

***Customer Number: 76681***

Please direct all correspondence in connection with said ***U.S. Patent Application(s) and/or Patent(s)*** to:

***Customer Number: 76681***

Respectfully submitted,

Date: 5/13/2008

Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

PATENT

**THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**STATEMENT UNDER 37 CFR 3.73(b)**

***MEMC Electronic Materials, Inc.***, a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in ***U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A.***

The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to ***MEMC Electronic Materials, Inc.*** via Assignment(s) recorded with the United States Patent and Trademark Office at the ***Reel/Frame Numbers on the attached Schedule A.***

The undersigned, ***Dr. Graham Fisher, Director of Intellectual Property,*** has full authorization to act on behalf of Assignee ***MEMC Electronic Materials, Inc.***

Respectfully submitted,

Date: 5/13/2008

Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

# APPENDIX A
## Owned by MEMC Electronic Materials, Inc.

| ATTORNEY REFERENCE | CONF. NO | PUBLICATION NO. & DATE | SERIAL NO. FILING DATE | PATENT NO. ISSUE DATE | CURRENT OWNER/ ASSIGNEE | REEL AND FRAME NO. | TITLE |
|---|---|---|---|---|---|---|---|
| MEMC2152 | 4683 | | 09/245,236 2/5/1999 | 6,197,088 2/13/2001 | MEMC Electronic Materials, Inc. | 009924/0736 | TUNGSTEN DOPED CRUCIBLE AND METHOD FOR PREPARING SAME |
| MEMC2153 | 9430 | | 09/172,546 10/14/1998 | 6,171,391 1/9/2001 | MEMC Electronic Materials, Inc. | 009572/0757 | METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL |
| MEMC2156 | 1712 | | 09/167,747 10/7/1998 | 6,039,801 3/21/2000 | MEMC Electronic Materials, Inc. | 009612/0596 | CONTINUOUS OXIDATION PROCESS FOR CRYSTAL PULLING APPARATUS |
| MEMC2172 | 3315 | | 09/082,906 5/21/1998 | 6,482,259 11/19/2002 | MEMC Electronic Materials, Inc. | 009807/0116 | PROCESS FOR THE REMOVAL OF COPPER AND OTHER METALLIC IMPURITIES FROM SILICON |
| MEMC2190 | 1689 | | 09/276,278 3/25/1999 | 6,227,944 5/8/2001 | MEMC Electronic Materials, Inc. | 009988/0581 | METHOD FOR PROCESSING A SEMICONDUCTOR WAFER |
| MEMC2232 | 2885 | | 09/352,980 7/14/1999 | 6,339,606 1/15/2002 | MEMC Electronic Materials, Inc. | 010222/0227 | PROCESS FOR FABRICATING SEMICONDUCTOR WAFERS WITH EXTERNAL GETTERING |
| MEMC2235.1 | 2260 | | 09/596,499 6/19/2000 | 6,458,202 10/1/2002 | MEMC Electronic Materials, Inc. | 011107/0117 | PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING UNIFORM THERMAL HISTORY |
| MEMC2246 | 1846 | | 09/345,934 7/1/1999 | 6,231,628 5/15/2001 | MEMC Electronic Materials, Inc. | 010256/0143 | METHOD FOR THE SEPARATION, REGENERATION AND REUSE OF AN EXHAUSTED GLYCOL-BASED SLURRY |
| MEMC2288 | 3920 | | 09/259,478 2/26/1999 | 6,197,111 3/6/2001 | MEMC Electronic Materials, Inc. | 009939/0094 | HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLER |
| MEMC2292 | 9668 | | 09/607,391 6/30/2000 | 6,599,815 7/29/2003 | MEMC Electronic Materials, Inc. | 011185/0935 | A METHOD AND APPARATUS FOR FORMING A SILICON WAFER WITH A DENUDED ZONE |
| MEMC2294 | 9659 | | 09/607,389 6/30/2000 | 6,339,016 1/15/2002 | MEMC Electronic Materials, Inc. | 011186/0967 | METHOD AND APPARATUS FOR FORMING AN EPITAXIAL SILICON WAFER WITH A DENUDED ZONE |
| MEMC2340.1 | 4591 | US 2002-0056410 A1 5/16/2002 | 09/972,608 10/5/2001 | 6,858,307 2/22/2005 | MEMC Electronic Materials, Inc. | 012409/0073 | METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON |
| MEMC2340.10 | 9176 | US-2005-0132946-A1 6/23/2005 | 11/059,885 2/16/2005 | 7,106,060 9/12/2006 | MEMC Electronic Materials, Inc. | Division of 09/972,608 recorded at 012409/0073 | METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON |
| MEMC2345 | 2610 | | 09/250,908 2/16/1999 | 6,284,384 9/4/2001 | MEMC Electronic Materials, Inc. | 009906/0976 | EPITAXIAL SILICON WAFER WITH INTRINSIC GETTERING |
| MEMC2345.1 | 3949 | US 2001-0032581 A1 10/25/2001 | 09/859,094 5/16/2001 | 6,527,855 3/25/2003 | MEMC Electronic Materials, Inc. | Division of 09/250,908 recorded at 009906/0976 | EPITAXIAL SILICON WAFER WITH INTRINSIC GETTERING AND A METHOD FOR THE PREPARATION THEREOF |
| MEMC2345.2 | 3292 | US2005-0096092 A1 5/12/2005 | 10/400,594 3/29/2003 | 8,956,092 10/25/2005 | MEMC Electronic Materials, Inc. | Division of 09/859,094 which is a division of 09/250,908 recorded at 009906/0976 | EPITAXIAL SILICON WAFER WITH INTRINSIC GETTERING AND A METHOD FOR THE PREPARATION THEREOF |
| MEMC2352 | 6473 | | 09/234,144 1/19/1999 | 6,053,974 4/25/2000 | MEMC Electronic Materials, Inc. | Division of 08/940,166 recorded at 008734/0188 | HEAT SHIELD FOR CRYSTAL PULLER |